

IN THE CLAIMS:

Please cancel claims 1-4, 6, 7, 10, 13 and 15 and add new claims 16 and 17. Please amend claims 5, 8, 9, 11, 12 and 14 as follows:

*A5
and
C1*
5. (Amended) The method for forming a semiconductor device according to claim 16, in which said step f1) includes:

depositing said second insulating film using a TEOS-CVD method utilizing TEOS activated by O₃.

A6
8. (Amended) The method for forming a semiconductor device according to claim 16, in which said step f2) includes forming a metal

wiring film by: a) depositing a TiN layer, and b) depositing an upper layer.

9. (Amended) The method for forming a semiconductor device according to claim 8, in which said step of forming a metal wiring film further includes heat-treating said TiN layer in a temperature range of 200 to 650°C after forming said TiN layer.

*A7
and
C2*
11. (Amended) The method for forming a semiconductor device according to claim 16, in which said step f2) includes forming a metal

wiring film by: a) depositing a base layer, and b) depositing an Al layer.

12. (Amended) The method for forming a semiconductor device according to claim 11, wherein

A1
C1
C3
C2

said step of depositing an Al layer comprises sputtering while heating said circuit board in a temperature range of 100 to 400°C.

A8

14. (Amended) The method for forming a semiconductor device according to claim 16, wherein

said step of forming said surface protective film comprises depositing SiN through a plasma-excitation CVD method having an RF power of 300 W or less.

Please add new claim 16.

16. (Newly Added) A method for forming a semiconductor device, comprising the steps of:

- 
- a) providing a circuit board;
 - b) forming a first insulating film at least indirectly on said circuit board;
 - c) forming a lower electrode on said first insulating film;
 - d) forming a ferroelectric film over said lower electrode;
 - e) forming an upper electrode over said ferroelectric film, said lower electrode, ferroelectric film, and upper electrode combining to form a ferroelectric capacitor;
 - f) creating a synthetic tensile stress upon said ferroelectric capacitor by:

*Ans
wtd*

f1) forming a second insulating film over said ferroelectric capacitor;

*Concl'd
C3*

f2) forming a metal wiring pattern over said second insulating film; and

f3) forming a surface protective film over said second insulating film and said metal wiring pattern.

Please add new claim 17:

17. (Newly Added) The method as in claim 16, in which step f1) includes forming a plurality of contact openings through said second insulating film for contacting said upper electrode and said lower electrode and step f2) includes providing contact between said metal wiring pattern and said upper and lower electrodes through said plurality of contact openings.

Respectfully Submitted,

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Kathleen Libby